

ANALYZING DEVICE WITH ELECTRON BEAM IRRADIATION

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Abstract

PURPOSE:To perform effectively average analysis of a wider zone of a specimen surface together with local analyses by allowing secondary radiations emitted from a specimen, which is placed in a place to receive irradiation of electron beam dispersed by an electron beam, to be irradiated on secondary radiations measuring device through a throttle.

CONSTITUTION:With possibility of coming in and going out, a radiations restricting throttle 5 is arranged at the electron beam focal point O of the objective lens 3 of an electron optical system for irradiation of electron beam (e) on the surface of a specimen, while a measuring device for secondary radiations from the specimen 8 is arranged so as to watch the focal point O. An electron lens 6 is arranged behind this throttle 5, and the electron beam (e) having passed the throttle 5 is dispersed to the zone to irradiate the whole specific region on the surface of specimen 8 placed below the electron lens 6. At this time, light emitted from the specimen surface, secondary radiations of X-rays is irradiated to the secondary radiations measuring device upon passing the throttle 5. This enables local analysis as well as average analyses over a wider zone.

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